

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Info
1	BRS	31	(process\$6 or react\$6) near chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:09		0
2	BRS	20	(process\$6 or react\$6) near chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:39		0
3	IS& R	2	("5344522").PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:13		0
4	BRS	31	(process\$6 or react\$6) near chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:32		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Condition	Errors
5	BRS	0	chemical near treat\$6 near chamber and vaccum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:41			0
6	BRS	13	treat\$6 and chamber and vaccum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:42			0
7	BRS	20	wafer with chamber and vaccum and temperature and control\$6 and gas and (substrate or wafer) with hold\$6 and heat\$6 and (hf or nh3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/25 00:42			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
8	BRS	0	(process\$6 or react\$6) and wash\$6 near chamber and vaccum and temperature and gas and (substrate or wafer) near hold\$6 near heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:11		0
9	BRS	0	wash\$6 near chamber and vaccum and temperature and gas and (substrate or wafer) near hold\$6 near heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:12		0
10	BRS	0	wash\$6 and chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6 with temperature with control\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:13		0
11	IS&R	2	("5344522").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:13		0
12	BRS	39	chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:06		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Errors
13	BRS	2	wash\$6 and chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 03:18			0
14	BRS	26	(wash\$6 or clean\$6) with (wafer or substrate) and chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:04			0
15	IS&R	2	("5254505").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:04			0
16	BRS	39	chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:08			0
17	BRS	2	loadlock near chamber and vaccum and temperature and gas and (substrate or wafer) with hold\$6 with heat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 08:08			0